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- (54) **SYSTEM AND METHOD FOR A PRE-DRIVER CIRCUIT**
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- (52) **U.S. Cl.**
CPC **H03K 17/687** (2013.01); **H03K 5/12** (2013.01); **H03K 19/0185** (2013.01)

(57) **ABSTRACT**

A drive circuit includes an input, a driver, a first buffer, a second buffer, a first capacitance element, and a second capacitance element. The driver includes a first PMOS transistor and a first NMOS transistor coupled in series between a supply terminal and a reference terminal. The first buffer is coupled between the input and a control terminal of the first PMOS transistor. The second buffer is coupled between the input and a control terminal of the first NMOS transistor. The first capacitance element is coupled to the control terminal of the first PMOS transistor through a first semiconductor switch. The second capacitance element is coupled to the control terminal of the first NMOS transistor through a second semiconductor switch.

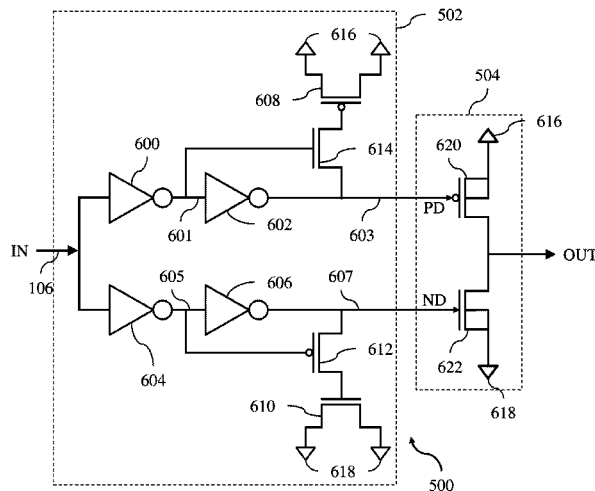
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28 Claims, 10 Drawing Sheets



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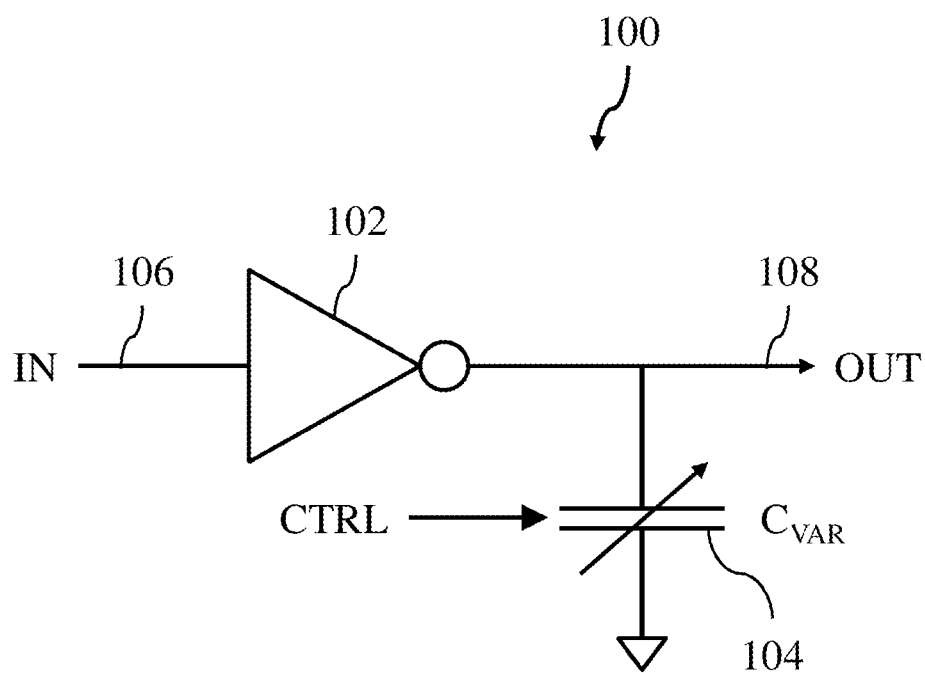
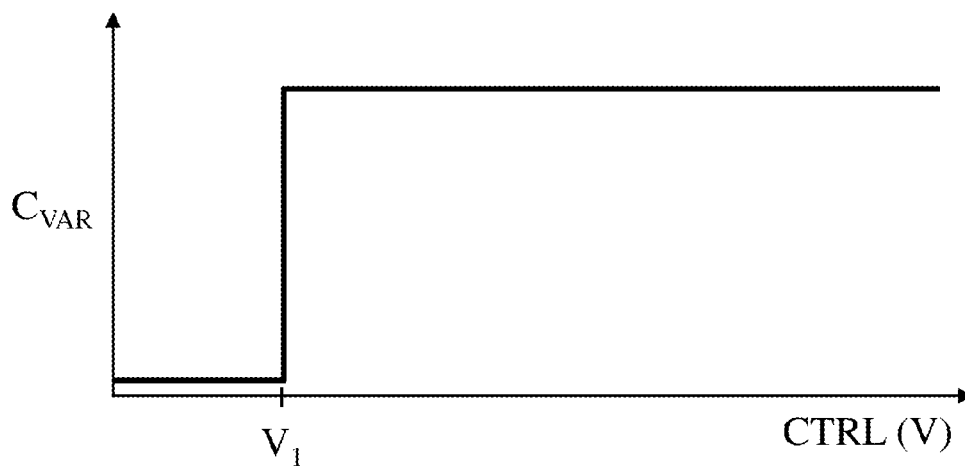
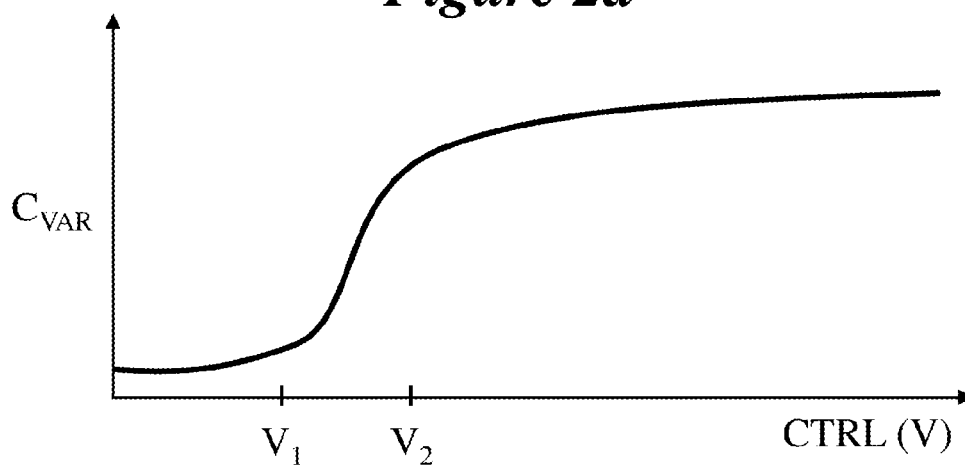
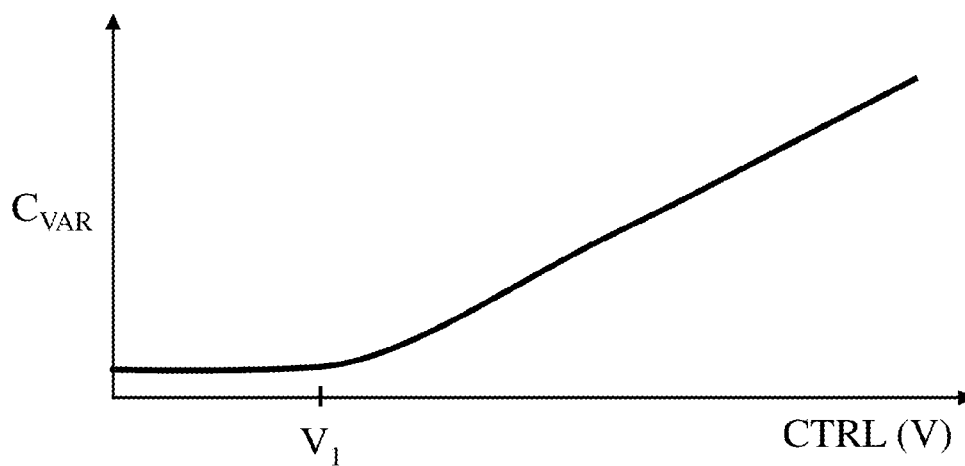
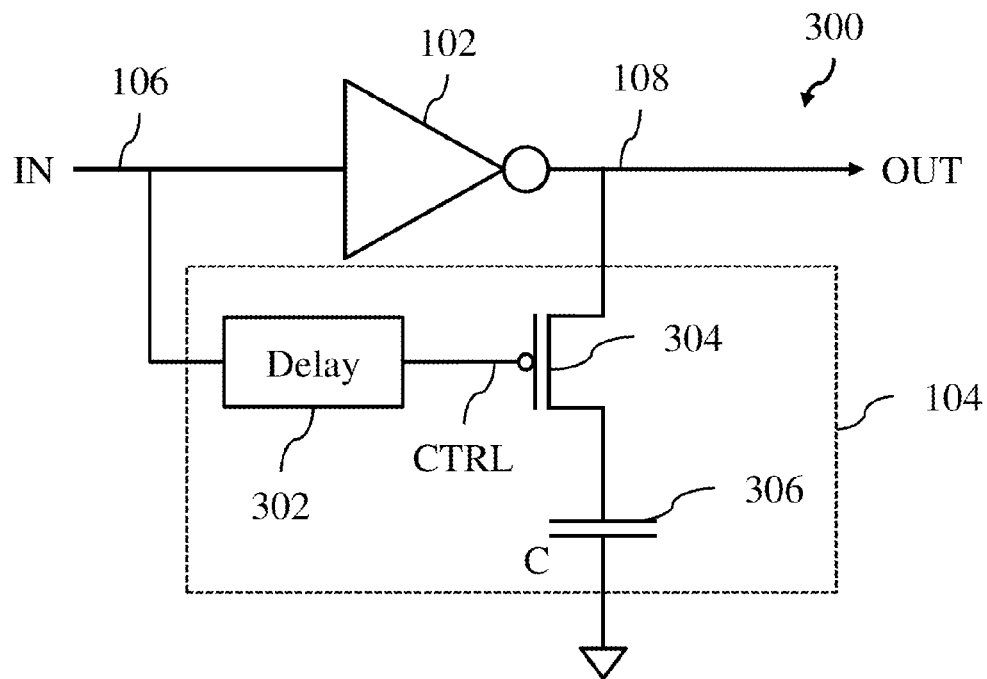
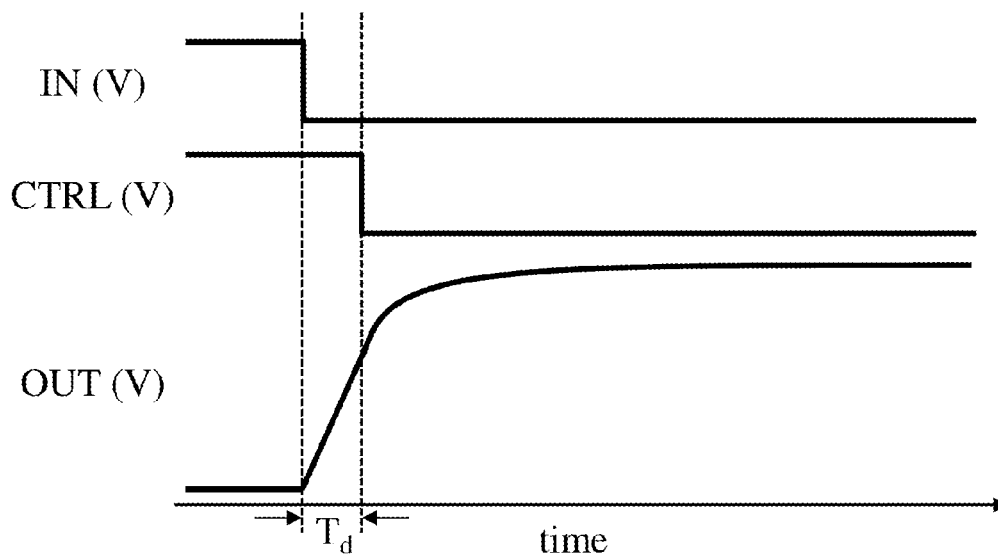


Figure 1

*Figure 2a**Figure 2b**Figure 2c*

*Figure 3a**Figure 3b*

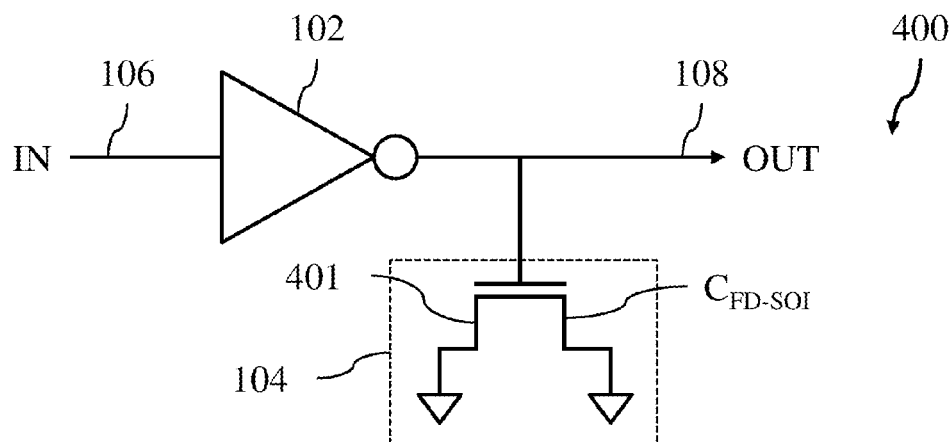


Figure 4a

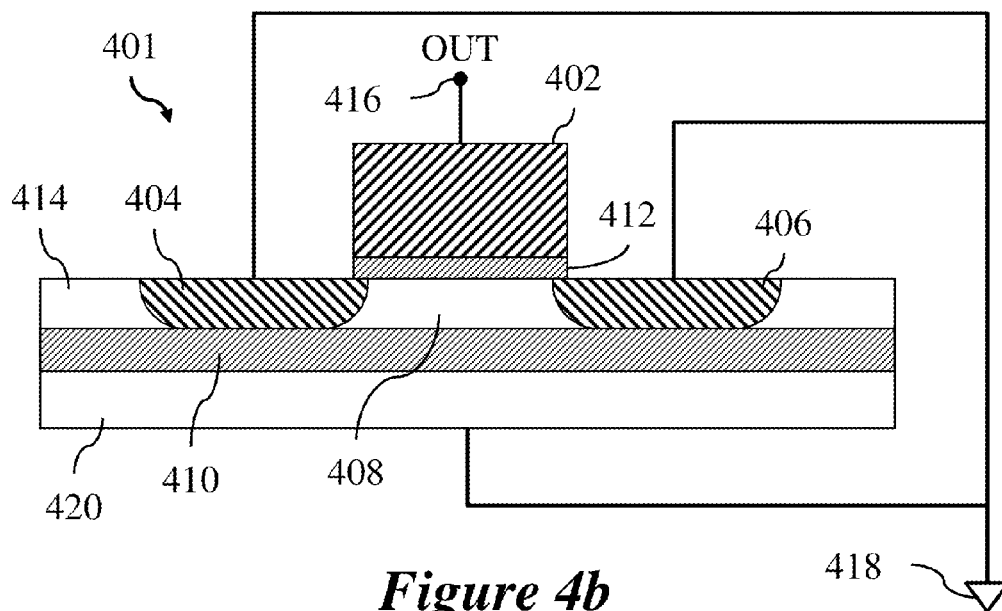


Figure 4b

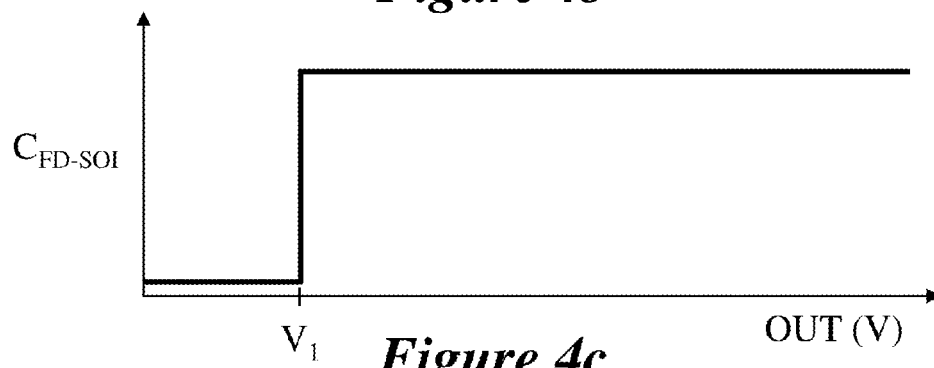


Figure 4c

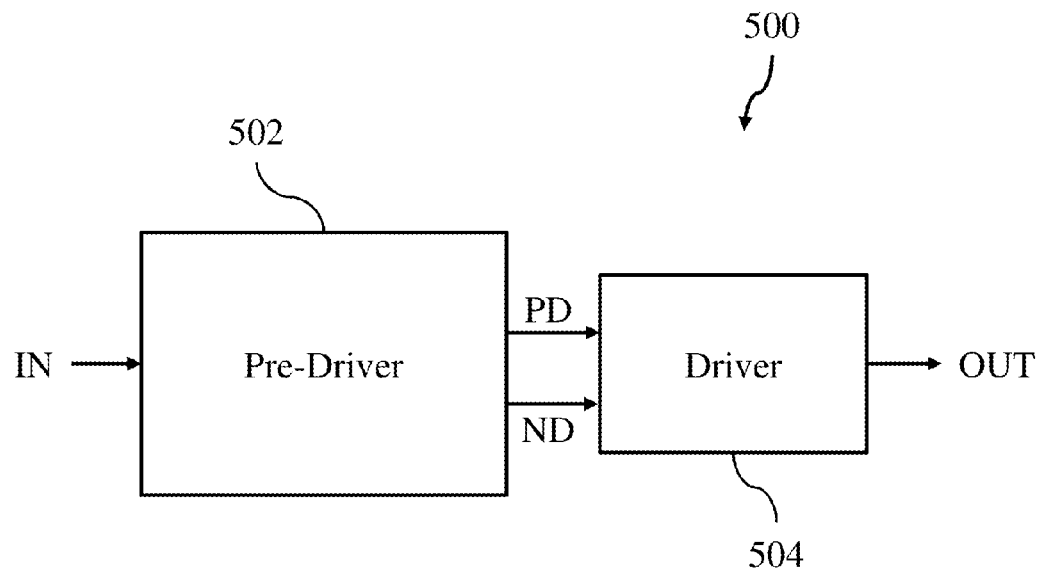


Figure 5

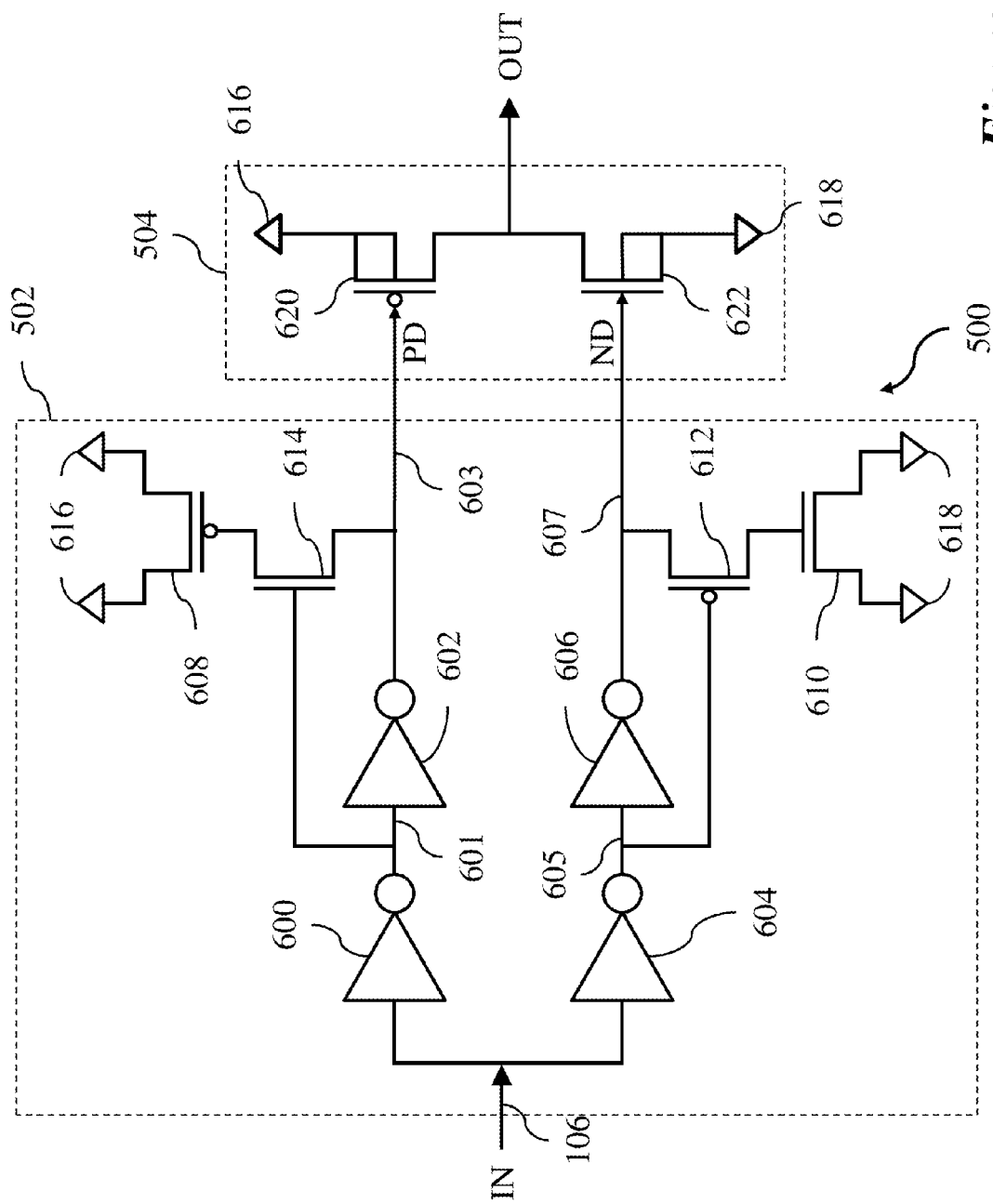


Figure 6

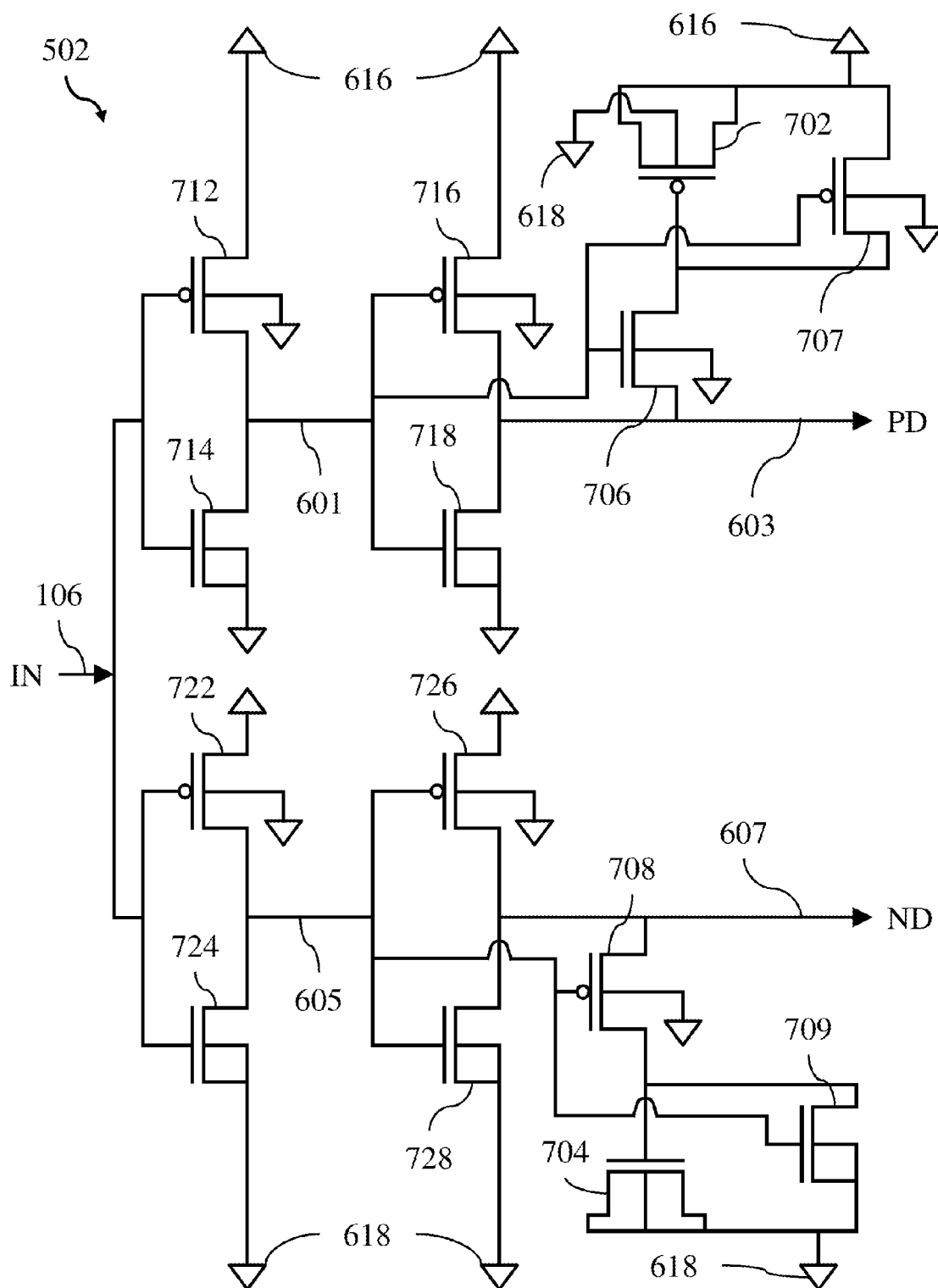


Figure 7

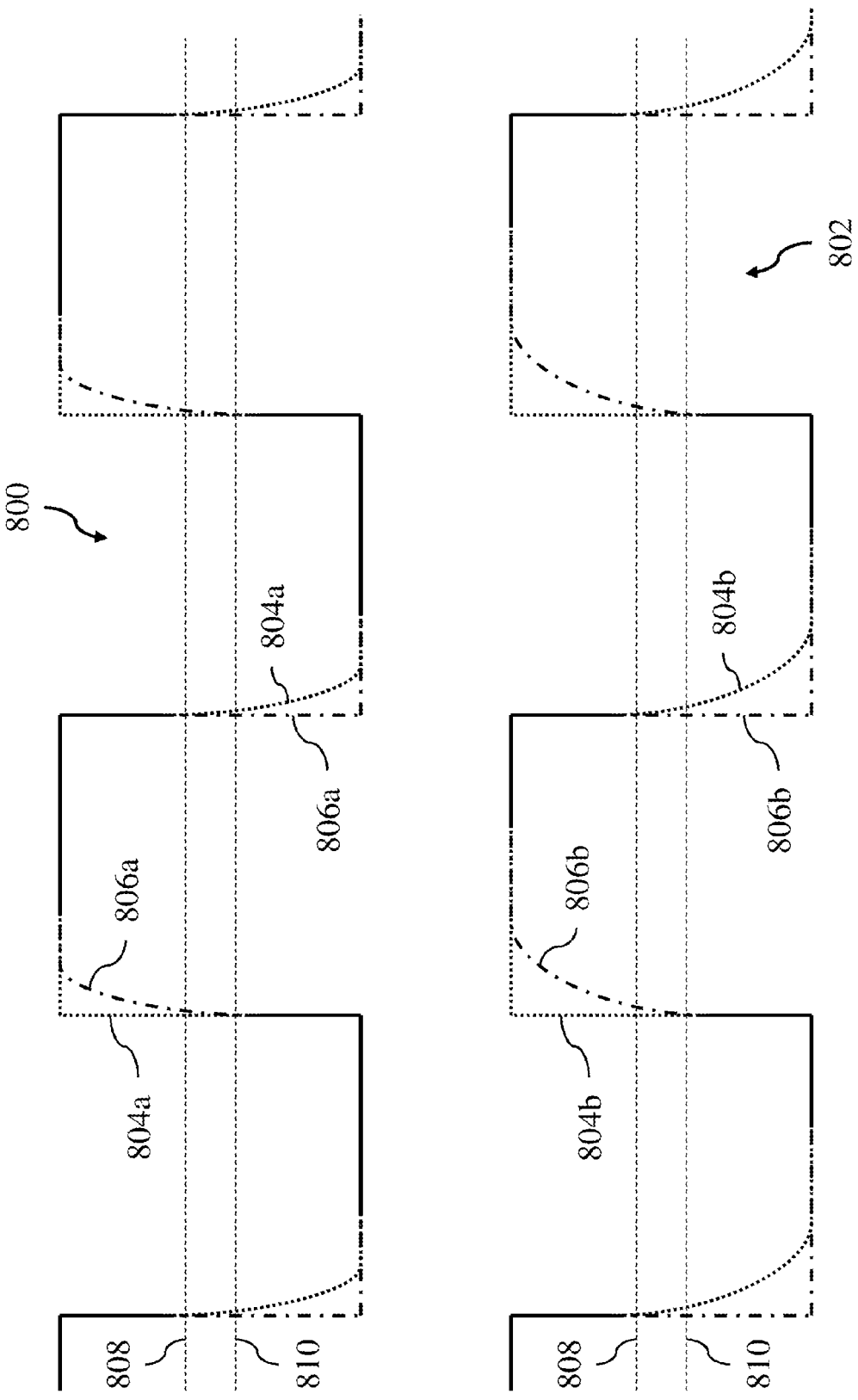
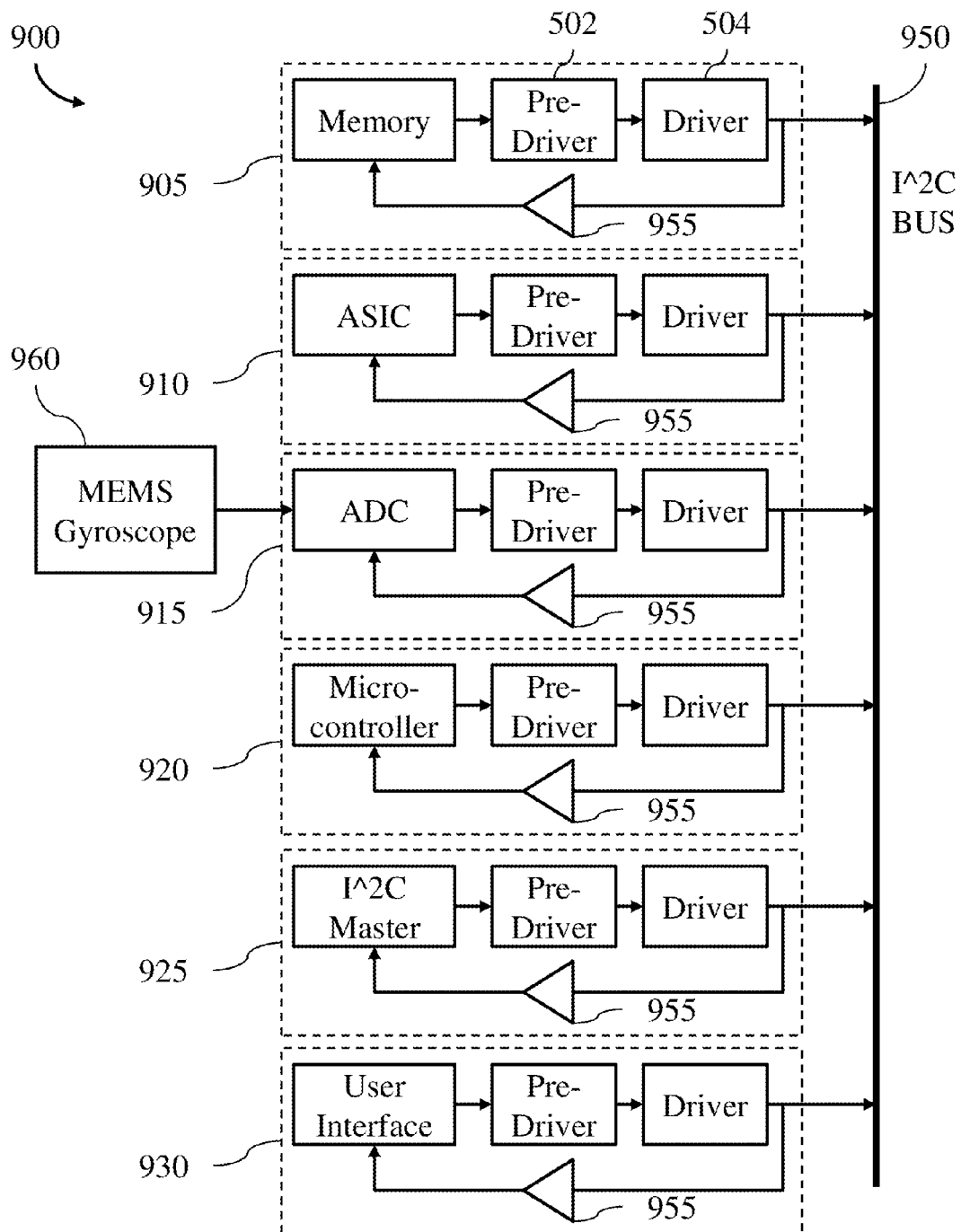
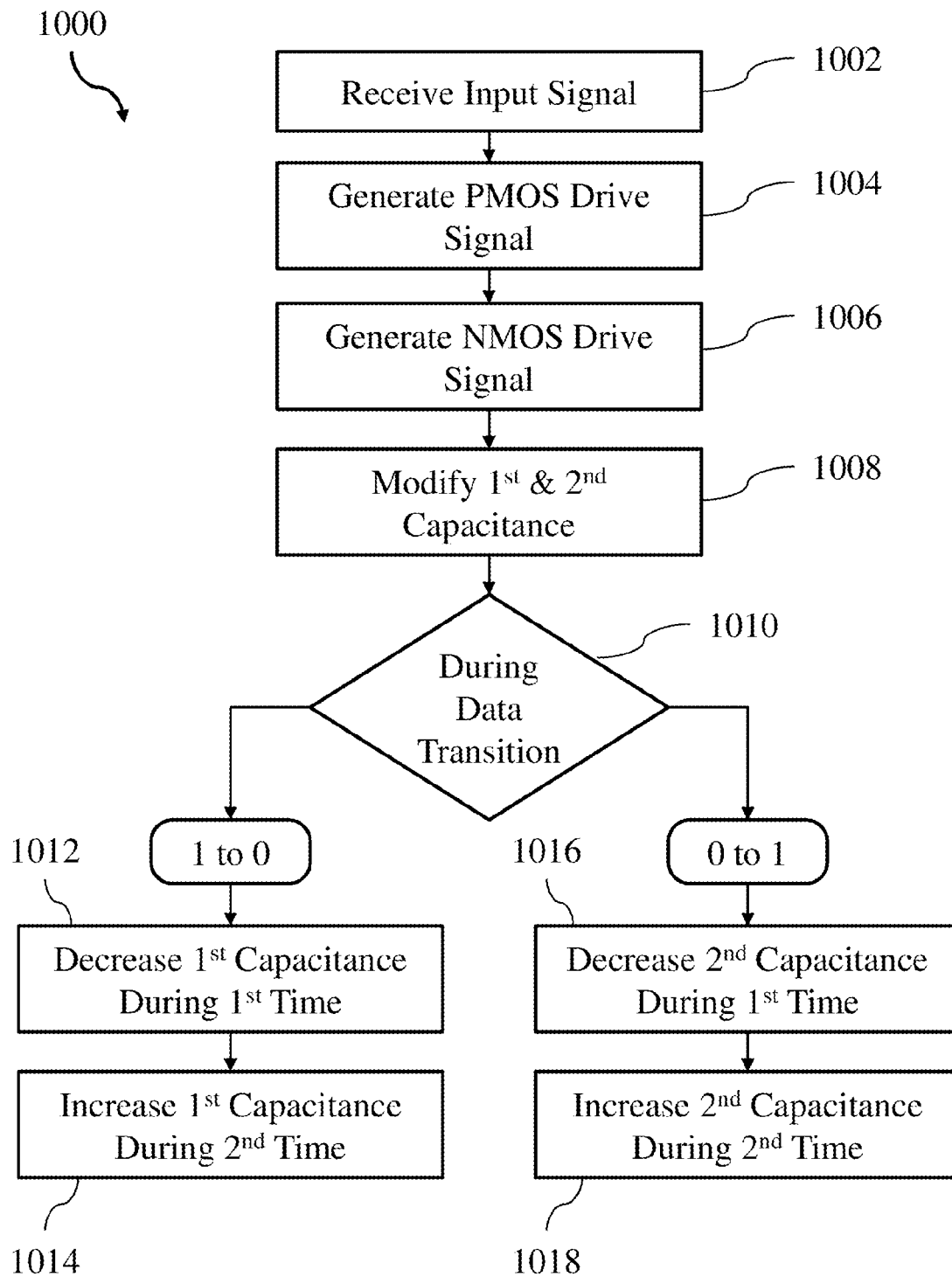


Figure 8

**Figure 9**

**Figure 10**

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SYSTEM AND METHOD FOR A PRE-DRIVER CIRCUIT

TECHNICAL FIELD

The present invention relates generally to electronic circuits and, in particular embodiments, to a system and method for a pre-driver circuit.

BACKGROUND

In many types of electronic circuits, a driver may be used to interface a control signal with a switch or output, for example. In some specific examples, drivers are used as output buffers for integrated circuits (ICs). In such examples, a driver is coupled to the output and configured to supply or drive an output that may be coupled to any type of electronic component, such as another IC, sensor, display, or actuator. In many instances, numerous components are coupled to an electronic bus that can convey signals between the components attached to the bus. In such cases, drivers are used to supply the signals originating at the components to the bus. Drivers may be operated to perform according to numerous specifications, such as operating with a specific output voltage and/or current, for example.

In some example implementations, drivers may operate at a higher voltage, current, and/or power rating than other electronic elements configured to supply control or drive signals to the driver. An element known as a pre-driver may be used before a driver in order to more precisely control the driver, e.g., because the electronic properties of the driver may not exactly match the other electronic elements of the system. The pre-driver is coupled to the driver and supplies the control signals to the driver circuit. A pre-driver may be configured to affect switching characteristics, such as on-time, rise-fall time, propagation delay, short circuit current, or other characteristics, for example.

A driver may be configured to provide an output signal and drive a bus connection while a pre-driver controls the driver based on signals received from digital electronics in the core of an IC. Pre-driver engineering often requires substantial balancing of beneficial performance characteristics and presents challenges suitable for inventive solutions.

SUMMARY OF THE INVENTION

A number of embodiments are disclosed herein.

A first embodiment relates to a drive circuit configured to drive an output line. A driver circuit includes a first PMOS transistor and a first NMOS transistor. The first PMOS transistor and the first NMOS transistor are coupled in series between a supply terminal and a reference terminal. A first buffer is coupled between the input and a control terminal of the first PMOS transistor. A second buffer is coupled between the input and a control terminal of the first NMOS transistor. A first capacitance element is coupled to the control terminal of the first PMOS transistor through a first semiconductor switch and a second capacitance element is coupled to the control terminal of the first NMOS transistor through a second semiconductor switch.

In various embodiments, the first and/or second capacitance elements can be formed from FD SOI transistors. For example, the first capacitance element can comprise a first fully depleted silicon-on-insulator (FD-SOI) transistor that includes a gate coupled to the control terminal of the first PMOS transistor and a source and drain coupled to a first reference terminal. The second capacitance element can

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comprise a second FD-SOI transistor that includes a gate coupled to the control terminal of the first NMOS transistor and a source and drain coupled to a second reference terminal.

In another embodiment, a pre-driver circuit includes first buffer coupled between an input terminal and a PMOS drive terminal and a second buffer coupled between the input terminal and an NMOS drive terminal. A first fully depleted silicon-on-insulator (FD-SOI) transistor includes a gate, source, and drain, where the source and drain are coupled to a first reference terminal. A first semiconductor switch has a conduction path coupled between the gate of the first FD-SOI transistor and the PMOS drive terminal. A second FD-SOI transistor includes a gate, source, and drain, where the source and drain are coupled to a second reference terminal. A second semiconductor switch has a conduction path coupled between the gate of the second FD-SOI transistor and the NMOS drive terminal.

Other embodiments are disclosed herein.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the present invention, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

FIG. 1 illustrates a schematic of an embodiment driver (e.g., pre-driver) circuit;

FIGS. 2a-2c illustrate capacitance plots for an embodiment driver circuit;

FIG. 3a illustrates a schematic of an additional embodiment driver circuit and FIG. 3b illustrates a timing diagram of the additional embodiment driver circuit;

FIG. 4a illustrates a schematic of a further embodiment driver circuit, FIG. 4b illustrates a schematic of the variable capacitor for the further embodiment driver circuit, and FIG. 4c illustrates an additional capacitance plot showing a characteristic FD-SOI capacitance;

FIG. 5 illustrates a block diagram of an embodiment pre-driver and driver system;

FIG. 6 illustrates a circuit diagram of an embodiment pre-driver and driver system;

FIG. 7 illustrates a more detailed circuit diagram of another embodiment pre-driver;

FIG. 8 illustrates waveform diagrams of outputs of embodiment pre-driver circuits;

FIG. 9 illustrates a schematic of an embodiment electronic system with an interface bus; and

FIG. 10 illustrates a block diagram of a method of operation of an embodiment system.

Corresponding numerals and symbols in the different figures generally refer to corresponding parts unless otherwise indicated. The figures are drawn to clearly illustrate the relevant aspects of the embodiments and are not necessarily drawn to scale.

DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

The making and using of various embodiments are discussed in detail below. It should be appreciated, however, that the various embodiments described herein are applicable in a wide variety of specific contexts. The specific embodiments discussed are merely illustrative of specific ways to make and use various embodiments, and should not be construed in a limited scope.

Description is made with respect to various embodiments in a specific context, namely input/output (I/O) circuits and interface circuits, and more particularly, pre-driver circuits. Some of the various embodiments described herein include drivers, pre-drivers, I/O interface circuits, variable capacitance pre-drivers, variable capacitance pre-drivers in fully depleted silicon-on-insulator (FD-SOI) integrated circuits, inverting drivers, and pre-drivers for bus interfaces. In other embodiments, aspects may also be applied to other applications involving any type of electronic interface or drive circuits according to any fashion as known in the art.

According to embodiments described herein, a driver has an increased rise-fall time with a decreased propagation delay. In electronic circuits, rapid transitions may be more affected by parasitic line inductance and/or capacitance, such as when switching at high frequencies. In order to reduce such parasitic behaviors, it may be beneficial to increase the rise or fall time during switching. According to embodiments, a driver system may include a pre-driver circuit to increase the rise-fall time by controlling a capacitance within the driver to control data transitions.

A capacitance that effects rise-fall time may also alter a propagation delay introduced by the driver circuit. According to embodiments described herein, a variable capacitance is used within a driver system to reduce propagation delay and increase rise-fall time. The capacitance may be controlled to be small during an initial portion of a transition and large during a final portion of the transition. Thus, according to various embodiments, an output signal is able to change quickly, reducing propagation delay, when a first capacitance is applied until a transition point and to change more slowly when a second capacitance is applied after the transition point. Thus, a driver is presented with a variable capacitance that allows the driver to have both a decreased propagation delay and an increased rise-fall time.

FIG. 1 illustrates a schematic of an embodiment driver circuit 100 including a driver 102 and a capacitance element 104 with a variable capacitance C_{VAR} . The driver 102 can be either inverting or non-inverting depending upon the application. As discussed below with respect to FIG. 5, the driver 102 can be implemented as a pre-driver.

According to various embodiments, driver 102 receives an input signal IN on terminal 106 and supplies an output signal OUT on terminal 108. Capacitor 104 may determine the output capacitance C_{VAR} on terminal 108 and may be altered using a control signal CTRL. The output capacitance C_{VAR} affects the rise-fall time of output signal OUT and the propagation delay of driver circuit 100. In some embodiments, the output capacitance C_{VAR} is controlled such that the value of output signal OUT changes quickly, but does not reach a final value as quickly because the output capacitance C_{VAR} is altered during a transition. In such embodiments, a propagation delay may be decreased while a rise-fall time is increased.

For further explanation, FIGS. 2a-2c illustrate capacitance plots for the embodiment driver circuit 100 and the output capacitance C_{VAR} . As shown, the vertical axis of the plots in FIGS. 2a-2c depicts output capacitance C_{VAR} and the horizontal axis depicts the control signal CTRL. In various embodiments, control signal CTRL is a voltage. In other embodiments, control signal CTRL may be implemented as a different type of signal, such as a current control signal, for example.

According to the embodiment shown in FIG. 2a, the output capacitance C_{VAR} is controlled in a way similar to a step function. During a first time period until control signal CTRL reaches V_1 , the output capacitance C_{VAR} is a small

value. In some embodiments, the output capacitance C_{VAR} is negligible or zero during the first time period. As shown, after control signal CTRL reaches V_1 , the output capacitance C_{VAR} increases to a larger value.

Referring to FIGS. 1 and 2a, driver circuit 100 may be operated to supply an output line on a bus and components connected thereto, for example. As discussed briefly above, transitions on the bus line may exhibit LC characteristics caused by non-ideal parasitic inductances or capacitances of interconnecting lines. In order to reduce the LC parasitic behavior, the rise-fall time is increased by the large output capacitance C_{VAR} . Consequently, in order to prevent the propagation delay of driver circuit 100 from increasing, the output capacitance C_{VAR} is decreased. Thus, FIG. 2a shows how the output capacitance C_{VAR} is decreased during a first time when the output signal OUT is transitioning. Reducing the output capacitance C_{VAR} allows the output signal OUT to transition very quickly. During a second portion of the transition, the output capacitance C_{VAR} is increased in order to increase the rise-fall time of the full transition of output signal OUT.

FIG. 2b illustrates another embodiment capacitance plot. As shown, the output capacitance C_{VAR} may exhibit other control characteristics compared to FIG. 2a. In such embodiments, the output capacitance C_{VAR} changes slightly until the control signal CTRL reaches a voltage V_1 , changes quickly as the control signal moves between voltages V_1 and V_2 , and then changes more slowly after V_2 , as shown in FIG. 2b.

FIG. 2c illustrates a further embodiment capacitance plot. As shown, the output capacitance C_{VAR} may be substantially constant at a low level until the control signal CTRL reaches V_1 and then may increase linearly as the control signal CTRL is increased thereafter. FIGS. 2a-2c are illustrative embodiments of various control schemes for the variable output capacitance C_{VAR} and are meant to show examples of the types of control relationships possible between the variable output capacitance C_{VAR} and the control signal CTRL. Other examples are also possible.

FIG. 3a illustrates a schematic of an additional embodiment driver circuit 300 that includes driver 102 and an implementation of variable capacitor 104 including delay block 302, transistor 304, and capacitor 306. In this embodiment, driver 102 is an inverting driver. As shown, delay block 302, transistor 304, and capacitor 306 are included in variable capacitor 104 and are one embodiment implementation. According to various embodiments, an input signal IN on terminal 106 triggers delay block 302 to turn-on transistor 304 after a delay time T_d (FIG. 3b). When transistor 304 is turned on, i.e. in a conducting state, the capacitance C of capacitor 306 is coupled to output terminal 108 with output signal OUT. In various embodiments, driver circuit 300 produces an output capacitance similar or identical to the output capacitance shown in FIG. 2a. Delay block 302 may be activated by a logic value of 1 or 0 in various embodiments and may be implemented as any known inverting or non-inverting delay block. In some embodiments, delay block 302 includes a series of any number of inverters, depending on the length of delay chosen. Capacitor 306 may be implemented as any type of capacitor and transistor 304 may be implemented as any type of transistor, such as a MOSFET, BJT, IGFET, FinFET, or FD-SOI transistor, for example.

FIG. 3b illustrates a timing diagram of the additional embodiment driver circuit 300. According to various embodiments, input signal IN transitions from a high level to a low level. Immediately after input signal IN transitions, output signal OUT begins to rapidly increase from 0 to 1

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during delay time T_d , during which time there is zero or negligible capacitance coupled to output terminal 108. After delay time T_d , which is generated by delay block 302, control signal CTRL, which is coupled to a control terminal of transistor 304, transitions from a high level to a low level and supplies an on-level activation signal to transistor 304. After control signal CTRL turns transistor 304 on, capacitor 306 is coupled to output terminal 108 causing a capacitively slowed change in output signal OUT.

FIG. 4a illustrates a schematic of a further embodiment driver circuit 400 that includes driver 102 and an implementation of variable capacitor 104 coupled to output terminal 108. According to various embodiments, variable capacitor 104 is implemented as a fully depleted silicon-on-insulator (FD-SOI) transistor connected as FD-SOI capacitor 401 with variable capacitance C_{FD-SOI} .

FIG. 4b illustrates a schematic of FD-SOI capacitor 401 for the embodiment driver circuit 400. FD-SOI capacitor 401 may also correspond to variable capacitor 104 in driver circuit 100. FD-SOI capacitor 401 includes gate 402, source 404, and drain 406. An FD-SOI process forms a buried insulator 410 on top of substrate 420. Substrate 420 may be a semiconductor body formed of silicon, for example. Silicon layer 414 may be formed on buried insulator 410. As shown, an area in silicon layer 414 between source 404 and drain 406 forms channel 408, which may be fully depleted of charge carriers. In some embodiments, silicon layer 414 is undoped. Insulation layer 412 separates channel 408 from gate 402.

According to various embodiments, source 404 and drain 406 may be raised above the level of silicon layer 414. Additionally, gate 402 may be insulated on its vertical sidewalls. In some particular embodiments, silicon layer 414 is less than 100 nm thick. In further embodiments, silicon layer 414 is less than 15 nm thick. Similarly, buried insulator 410 may be less than 200 nm thick. Further, buried insulator 410 may be less than 30 nm thick. Insulation layer 412 may be less than 50 nm, or less than 10 nm in further embodiments. In other embodiments, silicon layer 414, insulation layer 412, and buried insulator 410 may be any thickness.

In various embodiments, when a voltage above a certain threshold is applied to gate 402 through terminal 416 an inversion layer forms in channel 408. Terminal 416 may correspond to terminal 108 with output signal OUT in FIG. 1. A characteristic of FD-SOI is the variable capacitance that is formed between channel 408 and gate 402. In some embodiments, when an inversion layer is formed in channel 408, a large capacitance develops across insulation layer 412. However, when no inversion layer is formed, a negligible or small capacitance is present across insulation layer 412.

FIG. 4c illustrates an additional capacitance plot showing a characteristic FD-SOI capacitance C_{FD-SOI} . According to various embodiments, when a voltage below the turn-on voltage V_1 is applied, the capacitance C_{FD-SOI} of capacitor 401 is zero or small. When a voltage above the turn-on voltage V_1 is applied, capacitance C_{FD-SOI} is raised to a large value as shown. According to the embodiments shown in FIGS. 4a and 4b, the voltage is applied from output terminal 108 through terminal 416. Thus, the applied voltage is equal to output signal OUT, as shown by the capacitance plot in FIG. 4c. The shape of the capacitance C_{FD-SOI} may result from the feature that channel 408 is fully depleted. If no inversion layer forms in channel 408, there is no charge available for the bottom “plate” of the effective capacitor, which causes the effective capacitance to be very small or near zero. If an inversion layer forms in channel 408, a large

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amount of charge may be available for the bottom “plate” of the effective capacitor, which causes the effective capacitance to be large.

As shown in FIG. 4b, channel 408 with source 404 and drain 406 are coupled together to reference terminal 418. Thus, variable capacitor 104 is formed between terminals 416 and 418. Substrate 420 may be connected to a same reference terminal 418 as shown. In other embodiments, substrate 420 may be connected to another terminal or reference voltage. In various embodiments, reference terminal 418 may be a positive supply voltage VDD, negative supply voltage VSS, or a ground connection GND.

FIG. 5 illustrates a block diagram of an embodiment pre-driver and driver system 500 including pre-driver 502 and driver 504. Driver 504 may be configured to receive drive signals PD and ND from pre-driver 502 and provide an output signal OUT. Pre-driver 502 may receive an input control signal IN and produce drive signals PD and ND. Drive signal PD may be a PMOS drive signal and drive signal ND may be an NMOS drive signal. The circuits described with respect to FIGS. 1-4 can be used as the pre-driver 502.

In but one example, pre-driver 502 can be implemented as a three-phase motor pre-driver for automotive applications. For a three-phase motor, three of the circuits 502 would be included, one circuit driving each of the three phases of the motor. In one example, the pre-driver could be designed to control six external MOSFETs in bridge configuration to drive three-phase motors in automotive applications. All gate driver outputs could be controlled by separate inputs.

FIG. 6 illustrates a circuit diagram of an embodiment pre-driver and driver system 500 including implementations of pre-driver 502 and driver 504 according to one embodiment. As shown, driver 504 may be implemented as PMOS transistor 620 and NMOS transistor 622, which have a conduction path coupled in series between reference terminal 616 and reference terminal 618. In various embodiments, reference terminal 616 may be a positive supply voltage VDD and reference terminal 618 may be a negative supply voltage VSS or a ground connection GND. The node between PMOS transistor 620 and NMOS transistor 622 supplies output signal OUT, which may be coupled to a bus line or an off chip component, for example. PMOS transistor 620 is controlled at drive terminal 603 by drive signal PD and NMOS transistor 622 is controlled at drive terminal 607 by drive signal ND.

According to various embodiments, pre-driver 502 may be implemented with buffers 600-606. As shown, buffers 600-606 are inverters. Drive signal PD may have two cascaded inverters 600 and 602 and drive signal ND may have two cascaded inverters 604 and 606, as shown. Thus, in the embodiment shown, input signal IN is not inverted and is conveyed to PMOS transistor 620 and NMOS transistor 622 of driver 502. In other embodiments, any combination of buffers may be used, inverting or non-inverting.

A transistor connected as variable capacitor 608 may be coupled to drive terminal 603 through NMOS transistor 614 and a transistor connected as variable capacitor 610 may be coupled to drive terminal 607 through PMOS transistor 612, as shown. According to an embodiment, NMOS transistor 614 and PMOS transistor 612 are controlled at their respective control terminals by signals coupled to a node between buffers 600 and 602, for NMOS transistor 614, and between buffers 604 and 606, for PMOS transistor 612, as shown. According to various embodiments, variable capacitors 608 and 610 are implemented as FD-SOI capacitors as described in reference to FIG. 3. In the embodiment shown, variable

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capacitor **608** is a p-type FD-SOI capacitor and variable capacitor **610** is an n-type FD-SOI capacitor. In further embodiments, all transistors in FIG. **6** are implemented as FD-SOI transistors.

In various embodiments, a transition of input signal IN from 0 to 1 enables NMOS transistor **622** and disables PMOS transistor **620** by applying a logic high value drive signal ND to drive terminal **607** and a logic high drive signal PD to drive terminal **603**. The transition of input signal IN causes NMOS transistor **614** to be non-conducting and to disconnect variable capacitor **608** from drive terminal **603**. The same transition of input signal IN causes PMOS transistor **612** to be conducting and to connect variable capacitor **610** to drive terminal **607**.

Thus, a transition of input signal IN from 0 to 1 effectively modifies the capacitance of drive terminals **603** and **607** in order to increase the capacitance of drive terminal **607** and to decrease the capacitance of drive terminal **603**. Following similar logic, a transition of input signal IN in the opposite direction, from 1 to 0, effectively modifies the capacitance of drive terminals **603** and **607** in order to decrease the capacitance of drive terminal **607** and to increase the capacitance of drive terminal **603**.

According to various embodiments, variable capacitors **608** and **610** have charging times and transistors **612** and **614** have turn-on times. The charging times and/or turn-on times may cause the coupling of variable capacitors **608** and **610** to drive terminals **603** and **607** to be delayed by a time delay. Thus, drive terminals **603** and **607** may drive transistors **620** and **622** during a first time period with first capacitance values and during a second time period with second capacitance values. This concept is discussed in reference to FIGS. **2a-2c** and is further discussed in reference to FIG. **8** below.

In an alternative embodiment, which is not explicitly illustrated, the transistors **612** and **614** can be eliminated. In this case, the control terminals of variable capacitors **608** and **610** would be connected directly to the respective outputs of the pre-driver on terminals **603** and **607**. In such an embodiment, variable capacitors **608** and **610** would be another type of controllable capacitor that receives control signals from nodes **601** and **605**, respectively. As before, the capacitor **608** and **610** will operate to provide the desired capacitance value at the drive terminal during a switching transition. Thus, capacitor **608** would be controlled to have a small capacitance when NMOS transistor **622** is driven and capacitor **610** would be controlled to have a small capacitance when PMOS transistor **620** is driven. Conversely, capacitor **608** would be controlled to have a large capacitance when PMOS transistor **620** is driven and capacitor **610** would be controlled to have a large capacitance when NMOS transistor **622** is driven. This embodiment would be useful in an implementation where the delay in driving from high to low is desired to be different than the delay in driving from low to high.

FIG. **7** illustrates a more detailed circuit diagram of an implementation of pre-driver **502** having numerous FD-SOI transistors coupled as a non-inverting buffer between terminal **106** and PD and ND drive terminals **603** and **607**, as described above. Transistors **712-718** may be implementations of buffers **600** and **602** and transistors **722-728** may be implementations of buffers **604** and **606**. According to various embodiments, FD-SOI capacitors **702** and **704** are variable capacitors that may be coupled to PD and ND drive terminals **603** and **607** through transistors **706** and **708**.

Transistors **707** and **709** may be configured to short circuit FD-SOI capacitors **702** and **704** when they are not coupled to the respective drive terminal **603** and **607**. As shown,

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FD-SOI capacitor **702** is coupled to transistors **706** and **707** such that a control signal from intermediate terminal **601** either causes transistor **706** to couple FD-SOI capacitor **702** to PD drive terminal **603** or causes transistor **707** to form a short circuit across FD-SOI capacitor **702**. Similarly, FD-SOI capacitor **704** is coupled to transistors **708** and **709** such that a control signal from intermediate terminal **605** either causes transistor **708** to couple FD-SOI capacitor **704** to ND drive terminal **607** or causes transistor **709** to form a short circuit across FD-SOI capacitor **704**. In such an embodiment, FD-SOI capacitors **702** and **704** are discharged when not connected to PD and ND drive terminals **603** and **607**, respectively. In various embodiments, all transistors shown in FIG. **7** are FD-SOI transistors. In alternative embodiments, all transistors shown in FIG. **7** may be implemented as any type of transistor as is known in the art.

According to various embodiments, there are two types of p-type FD-SOI devices. As shown in FIG. **7**, FD-SOI capacitor **702** is a p-type device with a substrate contact coupled to a low reference terminal **618**, e.g., a ground terminal GND. Another type of p-type FD-SOI device may be used for FD-SOI capacitor **702** that has a substrate contact coupled to a high reference terminal **616**, e.g., a supply terminal VDD. In various embodiments, the operation of both types of p-type FD-SOI devices may be the same. In further embodiments, there are also two types of n-type FD-SOI devices.

FIG. **8** illustrates waveform diagrams **800** and **802** of outputs of embodiment pre-driver circuits. According to various embodiments, waveform diagram **800** depicts PD drive signal **804a** and ND drive signal **806a** and waveform diagram **802** depicts PD drive signal **804b** and ND drive signal **806b**. Waveform diagram **800** may correspond to a pre-driver circuit having a lower overall capacitance than the overall capacitance in the pre-driver circuit that corresponds to waveform diagram **802**. In some embodiments, the vertical axis is a drive voltage and the horizontal axis is time.

In various embodiments, both waveform diagrams **800** and **802** depict a distinct change in capacitance during data transitions. For example, for PD drive signals **804a** and **804b** during data transitions from 1 to 0, a first portion of each transition is shown as a vertical line and a second portion shows a capacitive type charging curve. In such embodiments, the vertical line corresponds to a first time period during which zero or negligible capacitance is coupled to a drive terminal conveying PD drive signal **804a** or **804b**. The capacitive type charging curve then corresponds to a second time period during which a non-zero capacitance is coupled to the drive terminal conveying PD drive signal **804a** or **804b**.

In a like manner, for ND drive signals **806a** and **806b** during data transitions from 0 to 1, a first portion of each transition is shown as a vertical line and a second portion shows a capacitive type charging curve. In such embodiments, the vertical line corresponds to a first time period during which zero or negligible capacitance is coupled to a drive terminal conveying ND drive signal **806a** or **806b**. The capacitive type charging curve then corresponds to a second time period during which a non-zero capacitance is coupled to the drive terminal conveying ND drive signal **806a** or **806b**.

According to various embodiments, threshold voltage **808** is the threshold voltage for PMOS transistors in a driver, such as driver **504** for example, and threshold voltage **810** is the threshold voltage for NMOS transistors in the driver. The PMOS transistors may be turned on for voltages below threshold voltage **808** and the NMOS transistors may be

turned on for voltage above threshold voltage **810**. Thus, in various embodiments, during data transitions from 0 to 1 an NMOS transistor in the driver will be switched on and during transitions from 1 to 0 a PMOS transistor in the driver will be switched on during the first time period, i.e. effectively before the capacitance is coupled to the corresponding drive terminal. After the NMOS or PMOS transistor in the driver is turned on, the capacitance may be coupled to the drive terminal and slow the rise-fall time of an output signal OUT as described above. Thus, according to such embodiments, turn-on times and corresponding propagation delays are kept short while rise-fall times are increased.

FIG. 9 illustrates a schematic of an embodiment electronic system **900** with an interface bus **950** coupled to system components **905**, **910**, **915**, **920**, **925**, and **930**. Each component **905**, **910**, **915**, **920**, **925**, and **930** contains a pre-driver **502** and a driver **504** according to various embodiments described herein. According to various embodiments, components **905**, **910**, **915**, **920**, **925**, and **930** are merely illustrative. Additional components may be included or fewer components may be included in other embodiments. Components **905**, **910**, **915**, **920**, **925**, and **930** are interfaced with interface bus **950** according to the Inter-Integrated Circuit (I²C or IIC) protocol as is known in the art. In other embodiments, any other type of communication interface protocol may be used.

According to various embodiments, component **905** is a memory, component **910** is an application specific integrated circuit (ASIC), component **915** is an analog to digital converter (ADC), component **920** is a microcontroller, component **925** is I²C master, and component **930** is a user interface, such as a touchscreen display. In one embodiment, these components are included in a cell-phone package and may be part of a larger system including numerous components. Each component, such as ASIC **910** includes a pre-driver **502**, a driver **504**, and a read buffer **955**. The pre-driver **502** and driver **504** operate as described above to drive signals onto interface bus **950** and buffer **955** operates to read signals from interface bus **950**. As shown, each component functions according to the I²C protocol in order to receive or send data on interface bus **950**.

As a further example, ADC **915** may interface with a sensor or other analog component, such as microelectromechanical system (MEMS) gyroscope **960** as shown. In various embodiments, MEMS gyroscope **960** operates to detect rotations of a system device, such as a cell phone for example, and conveys signals containing rotation information to ADC **915**. ADC **915** may then convert the analog rotation signals to digital rotation signals and send the digital signals along interface bus **950** to microcontroller **920** or ASIC **910**. Pre-driver **502** and driver **504** may be included in ADC **915** and convey signals from ADC **915** to interface bus **950** according to embodiments described hereinabove.

FIG. 10 illustrates a block diagram of a method of operation **1000** of an embodiment system including steps **1002-1018**. According to various embodiments, step **1002** includes receiving an input signal at an input to a pre-driver. Based on the input signal in step **1002**, step **1004** includes generating a PMOS drive signal on a PMOS drive terminal and step **1006** includes generating an NMOS drive signal on an NMOS drive terminal. Step **1008** includes modifying a first capacitance coupled to the PMOS drive terminal and a second capacitance coupled to the NMOS drive terminal. Modifying the first and second capacitances may be performed during transitions of the PMOS and NMOS drive signals. In various embodiments, modifying the first and second capacitances in step **1008** includes steps **1010-1018**.

Step **1010** may include selecting a data transition type on the input signal such that during a data transition from 1 to 0 step **1012** follows step **1010** and during a data transition from 0 to 1 step **1016** follows steps **1010**. For a data transition from 1 to 0, step **1012** includes decreasing the capacitance coupled to the PMOS drive terminal during a first portion of the data transition from 1 to 0. Further, step **1014** includes increasing the capacitance coupled to the PMOS drive terminal during a second portion of the data transition from 1 to 0. In further embodiments, during the data transition from 1 to 0, the capacitance coupled to the NMOS drive terminal is decreased during both the first and second portions of the data transition. For a data transition from 0 to 1, step **1016** includes decreasing the capacitance coupled to the NMOS drive terminal during a first portion of the data transition from 0 to 1. Further, step **1018** includes increasing the capacitance coupled to the NMOS drive terminal during a second portion of the data transition from 0 to 1. In further embodiments, during the data transition from 0 to 1, the capacitance coupled to the PMOS drive terminal is decreased during both the first and second portions of the data transition. In various embodiments, step **1008**, which may include steps **1010-1018**, may be repeated for multiple data transitions.

Advantages of embodiments described herein may include decreasing the propagation delay of a pre-driver and driver circuit and increasing the rise-fall time of a pre-driver and driver circuit. A further advantage may include decreasing the area on an integrated circuit devoted to pre-driver circuits.

An additional advantage may include removing or limiting the capacitance of a pre-driver output on a line that is not selected while increasing the capacitance of the pre-driver output on a line that is selected. In one embodiment, because the selected FD-SOI capacitor coupled to a pre-driver output matches the selected driver transistor, variations in performance of the transistor will match variations of performance of the capacitor such that variations are compensated or partially compensated. For example, variable capacitor **608** matches and compensates variations from transistor **620** and variable capacitor **610** matches and compensates variations from transistor **622**.

While this invention has been described with reference to illustrative embodiments, this description is not intended to be construed in a limiting sense. Various modifications and combinations of the illustrative embodiments, as well as other embodiments of the invention, will be apparent to persons skilled in the art upon reference to the description. It is therefore intended that the appended claims encompass any such modifications or embodiments.

What is claimed is:

1. A drive circuit comprising:

an input;

a driver comprising a first PMOS transistor and a first NMOS transistor, wherein the first PMOS transistor and the first NMOS transistor are coupled in series between a supply terminal and a reference terminal;

a first buffer coupled between the input and a control terminal of the first PMOS transistor;

a second buffer coupled between the input and a control terminal of the first NMOS transistor;

a first capacitance element coupled to the control terminal of the first PMOS transistor through a first semiconductor switch; and

a second capacitance element coupled to the control terminal of the first NMOS transistor through a second semiconductor switch, wherein

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the first capacitance element with the first semiconductor switch and the second capacitance element with the second semiconductor switch comprise variable capacitance elements,
 the variable capacitance elements are controlled such that
 the first capacitance element provides a capacitance value of substantially zero when the second capacitance element provides a non-zero capacitance value during a first portion of a data transition from 1 to 0 on the control terminal of the first PMOS transistor,
 the first capacitance element provides a non-zero capacitance value when the second capacitance element provides a capacitance value of substantially zero during a second portion of a data transition from 1 to 0 on the control terminal of the first PMOS transistor,
 the second capacitance element provides a capacitance value of substantially zero when the first capacitance element provides a non-zero capacitance value during a first portion of a data transition from 0 to 1 on the control terminal of the first NMOS transistor, and
 the second capacitance element provides a non-zero capacitance value when the first capacitance element provides a capacitance value of substantially zero during a second portion of a data transition from 0 to 1 on the control terminal of the first NMOS transistor.

2. The drive circuit of claim 1, wherein
 the first capacitance element comprises a first fully depleted silicon-on-insulator (FD-SOI) transistor including a gate coupled to the control terminal of the first PMOS transistor and a source and drain coupled to a first reference terminal; and
 the second capacitance element comprises a second FD-SOI transistor including a gate coupled to the control terminal of the first NMOS transistor and a source and drain coupled to a second reference terminal.

3. The drive circuit of claim 1, wherein the supply terminal and the reference terminal are both configured to carry the same reference voltage.

4. A pre-driver circuit comprising:
 an input node;
 a first buffer with an input coupled to the input node and an output configured to be coupled to a first control terminal of a drive circuit;
 a second buffer with an input coupled to the input node and an output configured to be coupled to a second control terminal of the drive circuit;
 a first semiconductor switch;
 a first capacitance element coupled to the output of the first buffer through the first semiconductor switch;
 a second semiconductor switch; and
 a second capacitance element coupled to the output of the second buffer through the second semiconductor switch, wherein the first and second semiconductor switches are configured to receive control signals coupled to the input node and wherein the control signals are configured to:
 disable the first semiconductor switch during a first portion of a data transition from 1 to 0 at the output of the first buffer;
 enable the first semiconductor switch during a second portion of a data transition from 1 to 0 at the output of the first buffer;

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disable the second semiconductor switch during a first portion of a data transition from 0 to 1 at the output of the second buffer; and
 enable the second semiconductor switch during a second portion of a data transition from 0 to 1 at the output of the second buffer.

5. The pre-driver circuit of claim 4, wherein
 the first capacitance element comprises a first fully depleted silicon-on-insulator (FD-SOI) transistor including a gate coupled to the output of the first buffer and a source and drain coupled to a first reference terminal; and
 the second capacitance element comprises a second FD-SOI transistor including a gate coupled to the output of the second buffer and a source and drain coupled to a second reference terminal.

6. The pre-driver circuit of claim 5, wherein the first reference terminal is configured to carry a first reference voltage and the second reference terminal is configured to carry a second reference voltage different than the first reference voltage.

7. The pre-driver circuit of claim 6, wherein the first reference terminal comprises a supply terminal of the pre-driver circuit and the second reference terminal comprises a reference terminal of the pre-driver circuit.

8. The pre-driver circuit of claim 5, wherein the first reference terminal and the second reference terminal are both configured to carry the same reference voltage.

9. The pre-driver circuit of claim 5, wherein:
 the first semiconductor switch comprises a second NMOS transistor including a gate and a conduction path coupled between the gate of the first FD-SOI transistor and the output of the first buffer; and
 the second semiconductor switch comprises a second PMOS transistor including a gate and a conduction path coupled between the gate of the second FD-SOI transistor and the output of the second buffer.

10. The pre-driver circuit of claim 9, wherein
 the first buffer comprises a first inverter coupled between the input and a first intermediate node and a second inverter coupled between the first intermediate node and the output of the first buffer;
 the second buffer comprises a third inverter coupled between the input and a second intermediate node and a fourth inverter coupled between the second intermediate node and the output of the second buffer; and
 the gate of the second NMOS transistor is coupled to the first intermediate node and the gate of the second PMOS transistor is coupled to the second intermediate node.

11. The pre-driver circuit of claim 10, further comprising:
 a third PMOS transistor including a gate coupled to the first intermediate node and a conduction path coupled between the first reference terminal and the gate of the first FD-SOI transistor; and
 a third NMOS transistor including a gate coupled to the second intermediate node and a conduction path coupled between the second reference terminal and the gate of the second FD-SOI transistor.

12. The pre-driver circuit of claim 11, wherein the second and third NMOS and PMOS transistors are FD-SOI transistors.

13. The pre-driver circuit of claim 4, wherein the first capacitance element and the second capacitance element comprises variable capacitance elements.

14. The pre-driver circuit of claim 13, wherein the first and second capacitance elements are controlled such that the

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first capacitance element has a capacitance value of substantially zero when the second capacitance element has a non-zero capacitance value and wherein the second capacitance element has a capacitance value substantially zero when the first capacitance element has a non-zero capacitance value.

15. A pre-driver comprising:

- a first buffer coupled between an input terminal and a PMOS drive terminal;
- a second buffer coupled between the input terminal and an NMOS drive terminal;
- a first fully depleted silicon-on-insulator (FD-SOI) transistor comprising a gate, source, and drain, wherein the source and drain are coupled to a first reference terminal;
- a first semiconductor switch having a conduction path coupled between the gate of the first FD-SOI transistor and the PMOS drive terminal;
- a second FD-SOI transistor comprising a gate, source, and drain, wherein the source and drain are coupled to a second reference terminal; and
- a second semiconductor switch having a conduction path coupled between the gate of the second FD-SOI transistor and the NMOS drive terminal, wherein the first and second semiconductor switches are configured to receive control signals coupled to the input terminal and wherein the control signals are configured to:
 - disable the first semiconductor switch during a first portion of a data transition from 1 to 0 on the PMOS drive terminal;
 - enable the first semiconductor switch during a second portion of a data transition from 1 to 0 on the PMOS drive terminal;
 - disable the second semiconductor switch during a first portion of a data transition from 0 to 1 on the NMOS drive terminal; and
 - enable the second semiconductor switch during a second portion of a data transition from 0 to 1 on the NMOS drive terminal.

16. The pre-driver of claim 15, wherein the control signals are further configured to disable the second semiconductor switch during the first and second portions of the data transition from 1 to 0 on the PMOS drive terminal and to disable the first semiconductor switch during the first and second portions of the data transition from 0 to 1 on the NMOS drive terminal.

17. The pre-driver of claim 15, further comprising a driver coupled to the PMOS drive terminal and the NMOS drive terminal, wherein the driver comprises:

- a PMOS transistor including a gate coupled to the PMOS drive terminal and a conduction path coupled between the first reference terminal and an output terminal; and
- an NMOS transistor including a gate coupled to the NMOS drive terminal and a conduction path coupled between the output terminal and the second reference terminal.

18. The pre-driver of claim 17, wherein the driver is configured to drive signals on a circuit bus through the output terminal.

19. The pre-driver of claim 18, wherein the circuit bus is configured to operate with an I²C protocol.

20. A pre-driver comprising:

- a first buffer coupled between an input terminal and a PMOS drive terminal;
- a second buffer coupled between the input terminal and an NMOS drive terminal;

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a first fully depleted silicon-on-insulator (FD-SOI) transistor comprising a gate, source, and drain, wherein the source and drain are coupled to a first reference terminal;

a first semiconductor switch having a conduction path coupled between the gate of the first FD-SOI transistor and the PMOS drive terminal;

a second FD-SOI transistor comprising a gate, source, and drain, wherein the source and drain are coupled to a second reference terminal;

a second semiconductor switch having a conduction path coupled between the gate of the second FD-SOI transistor and the NMOS drive terminal;

a third semiconductor switch having a conduction path coupled between the first reference terminal and the gate of the first FD-SOI transistor; and

a fourth semiconductor switch having a conduction path coupled between the second reference terminal and the gate of the second FD-SOI transistor, wherein the third and fourth semiconductor switches are configured to receive a control signal coupled to the input terminal.

21. A method of driving a terminal, the method comprising:

- receiving an input signal;
- generating a PMOS drive signal on a PMOS drive terminal based on the input signal;
- generating an NMOS drive signal on an NMOS drive terminal based on the input signal; and
- modifying a first capacitance coupled to the PMOS drive terminal and a second capacitance coupled to the NMOS drive terminal during transitions of the PMOS and NMOS drive signals, wherein modifying the first and second capacitance comprises:
 - during a first data transition from 1 to 0 for the PMOS drive signal, decreasing the capacitance coupled to the PMOS drive terminal during a first portion of the first data transition and increasing the capacitance coupled to the PMOS drive terminal during a second portion of the first data transition, and
 - during a second data transition from 0 to 1 for the NMOS drive signal, decreasing the capacitance coupled to the NMOS drive terminal during a first portion of the second data transition and increasing the capacitance coupled to the NMOS drive terminal during a second portion of the second data transition.

22. The method of claim 21, further comprising:

- during the first data transition from 1 to 0 for the PMOS drive signal, decreasing the capacitance coupled to the NMOS drive terminal during the first and second portions of the first data transition; and
- during the second data transition from 0 to 1 for the NMOS drive signal, decreasing the capacitance coupled to the PMOS drive terminal during the first and second portions of the second data transition.

23. An integrated circuit comprising:

- a semiconductor body;
- a reference node conductor overlying the semiconductor body;
- a buried insulator within the semiconductor body;
- a fully depleted channel within the semiconductor body over the buried insulator;
- a gate electrode overlying the fully depleted channel and insulated from the semiconductor body;
- a first source/drain within the semiconductor body and coupled to the reference node conductor;
- a second source/drain within the semiconductor body and coupled to the reference node conductor, the second

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source/drain spaced from the first source/drain by the fully depleted channel; and
 a buffer disposed at a surface of the semiconductor body, the buffer comprising an input terminal configured to receive an input signal and an output terminal directly connected to the gate electrode. 5

24. The integrated circuit of claim 23, further comprising a semiconductor switch disposed at the surface of the semiconductor body, the semiconductor switch having a conduction path between the output terminal of the buffer and the gate electrode so that the output terminal is electrically coupled to the gate electrode when the semiconductor switch is in a conductive mode. 10

25. The integrated circuit of claim 23, wherein the semiconductor body is electrically coupled to the reference node conductor. 15

26. The integrated circuit of claim 23, wherein the output terminal of the buffer is configured to be coupled to an input of a driver circuit, the driver circuit comprising an NMOS transistor and a PMOS transistor. 20

27. The integrated circuit of claim 26, wherein the buffer comprises an inverter.

28. An integrated circuit comprising:

a semiconductor body;
 a reference node conductor overlying the semiconductor body; 25

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a buried insulator within the semiconductor body;
 a fully depleted channel within the semiconductor body over the buried insulator;
 a gate electrode overlying the fully depleted channel and insulated from the semiconductor body;
 a first source/drain within the semiconductor body and coupled to the reference node conductor;
 a second source/drain within the semiconductor body and coupled to the reference node conductor, the second source/drain spaced from the first source/drain by the fully depleted channel;
 a buffer disposed at a surface of the semiconductor body, the buffer comprising an input terminal configured to receive an input signal and an output terminal electrically coupled to the gate electrode;
 a semiconductor switch disposed at the surface of the semiconductor body, the semiconductor switch having a conduction path between the output terminal of the buffer and the gate electrode so that the output terminal is electrically coupled to the gate electrode when the semiconductor switch is in a conductive mode; and
 a second semiconductor switch disposed at the surface of the semiconductor body, the second semiconductor switch including a conduction path coupled between the gate electrode and the reference node conductor.

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